

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[IXYS Corporation](#)

[IXFH40N50Q2](#)

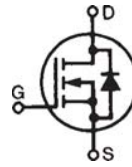
For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)



# HiPerFET™ Power MOSFETs Q2-Class

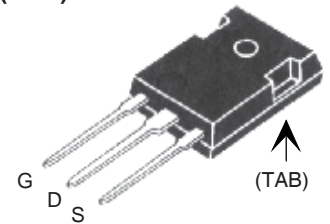
## IXFH40N50Q2



$$\begin{aligned}
 V_{DSS} &= 500V \\
 I_{D25} &= 40A \\
 R_{DS(on)} &\leq 160m\Omega \\
 t_{rr} &\leq 250ns
 \end{aligned}$$

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $Q_g$   
Low intrinsic  $R_g$ , low  $t_{rr}$

TO-247 (IXFH)



G = Gate  
S = Source

D = Drain  
TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	40	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	160	A
$I_A$	$T_C = 25^\circ\text{C}$	40	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	2.5	J
dV/dt	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	560	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.063 in) from case for 10s	300	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

### Features

- Double metal process for low gate resistance
- International standard package
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

- Easy to mount
- Space savings
- High power density

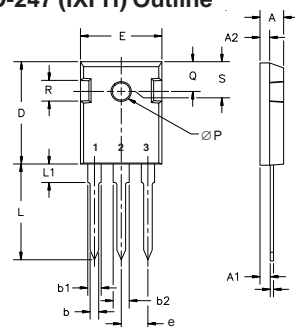
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ <span style="float: right;"><math>T_J = 125^\circ\text{C}</math></span>			25 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			160 m $\Omega$

# IXYS

## IXFH40N50Q2

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	15	28	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		4850	pF
$C_{oss}$			680	pF
$C_{rss}$			170	pF
$t_{d(on)}$	Resistive Switching Times		17	ns
$t_r$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		13	ns
$t_{d(off)}$	$R_G = 2\Omega$ (External)		42	ns
$t_f$			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		110	nC
$Q_{gs}$			25	nC
$Q_{gd}$			50	nC
$R_{thJC}$			0.22	$^\circ\text{C/W}$
$R_{thCK}$		0.21		$^\circ\text{C/W}$

### TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

### Source-Drain Diode

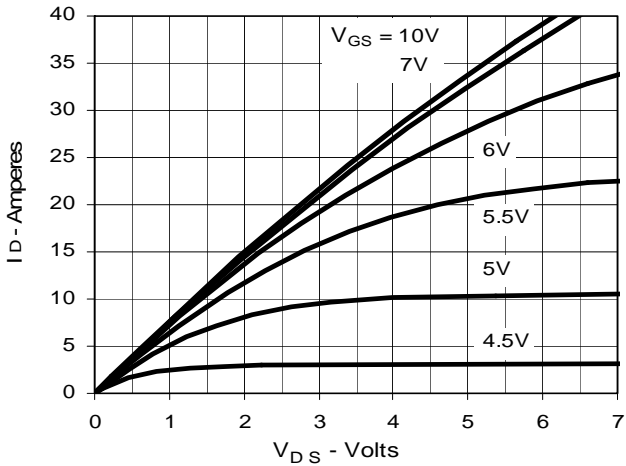
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			40 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			160 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}$			250 ns
$Q_{RM}$			1	$\mu\text{C}$
$I_{RM}$			9	A

 Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

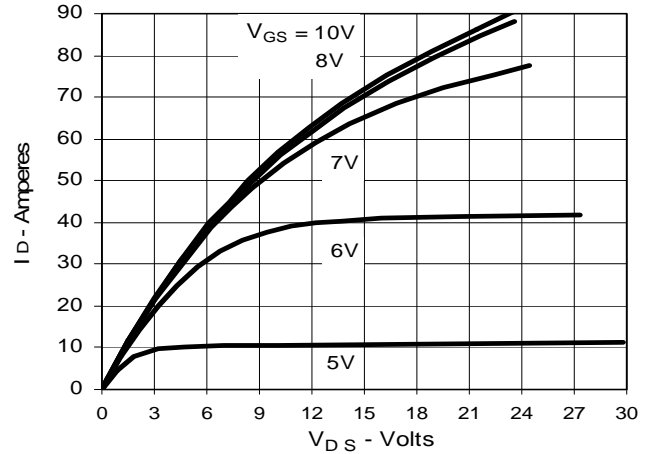
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

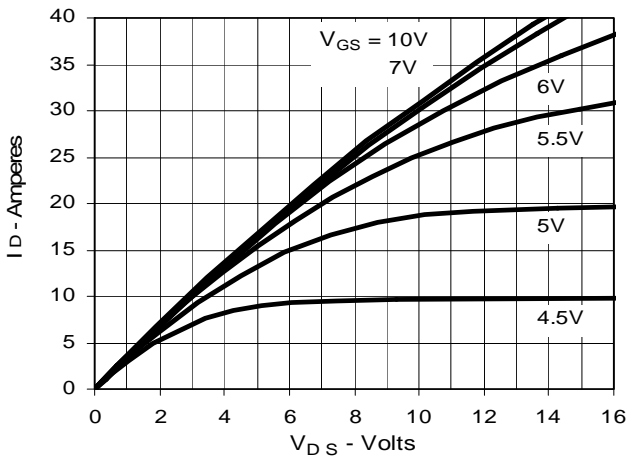
**Fig. 1. Output Characteristics**  
@ 25°C



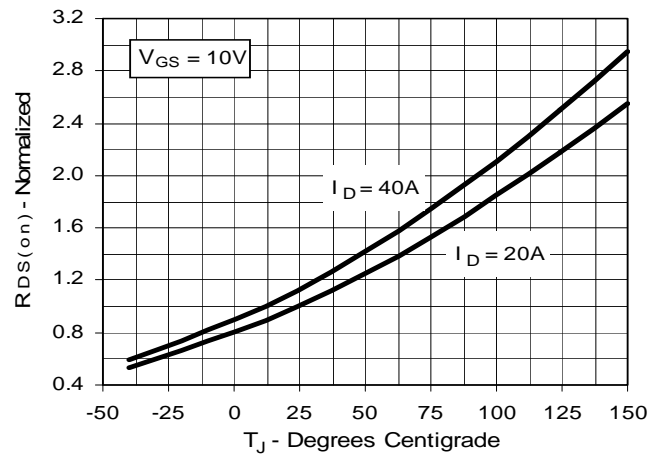
**Fig. 2. Extended Output Characteristics**  
@ 25°C



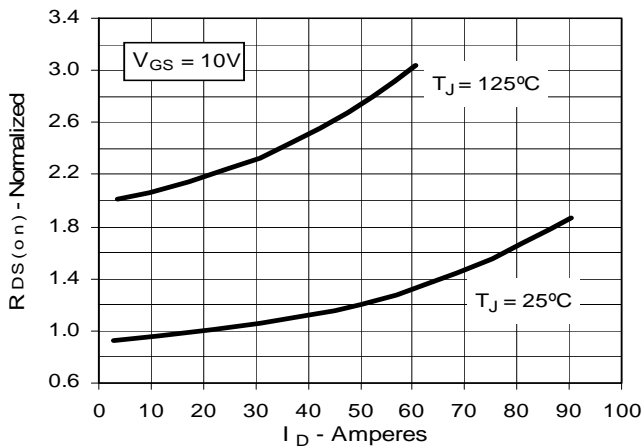
**Fig. 3. Output Characteristics**  
@ 125°C



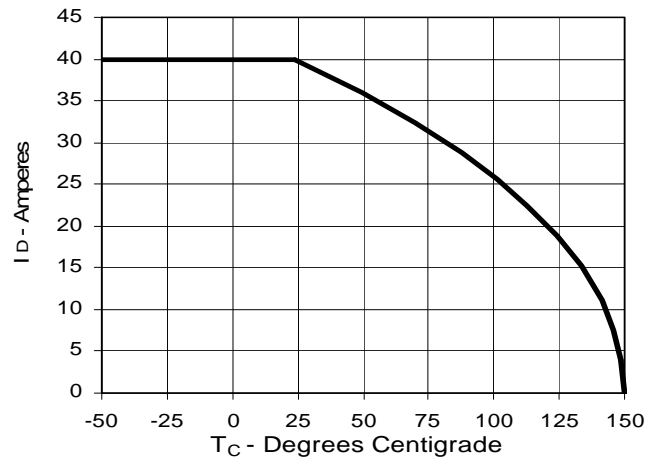
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



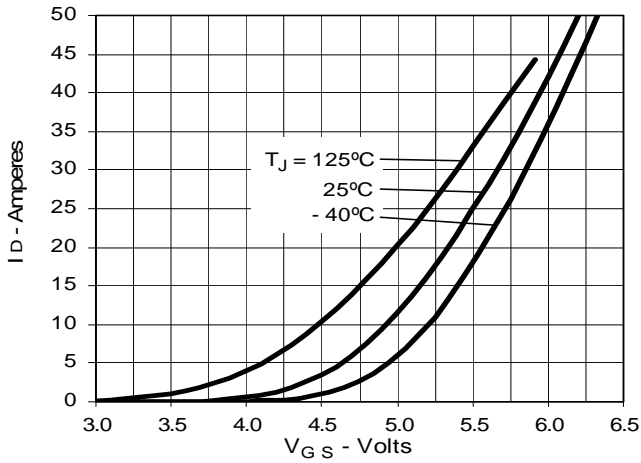
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



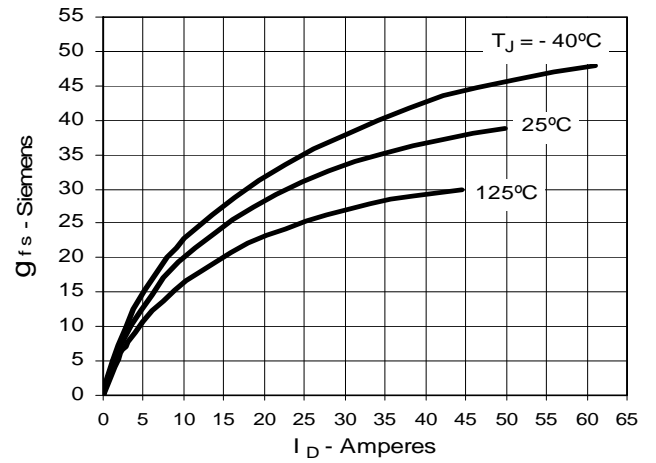
**Fig. 6. Drain Current vs. Case Temperature**



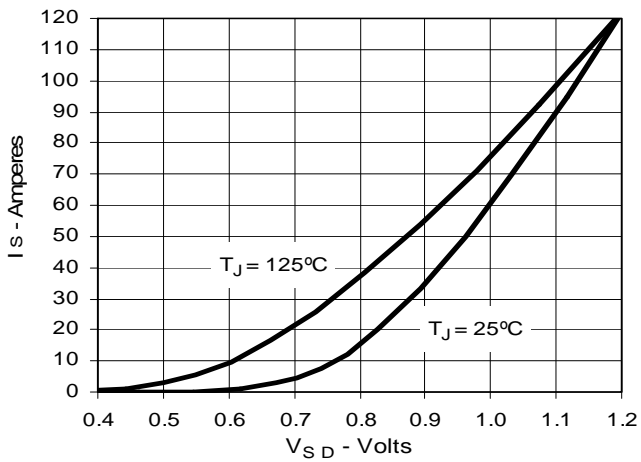
**Fig. 7. Input Admittance**



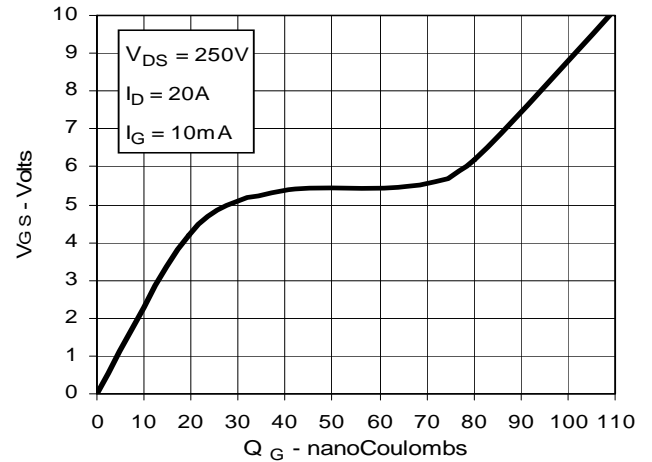
**Fig. 8. Transconductance**



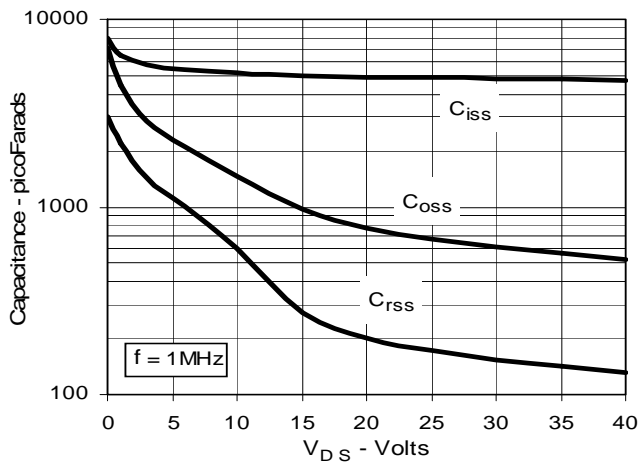
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



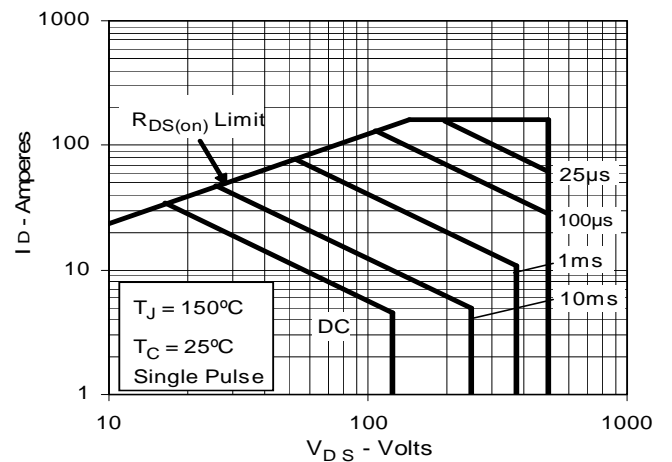
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



**Fig. 13. Maximum Transient Thermal Impedance**

